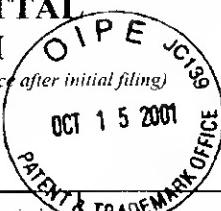
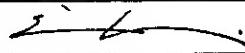


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<b>TRANSMITTAL FORM</b> <i>(to be used for all correspondence after initial filing)</i>		<b>Application Number</b>	09/433,705
		<b>Filing Date</b>	November 4, 1999
		<b>First Named Inventor</b>	Shunpei YAMAZAKI
		Group Art Unit	2811
		Examiner Name	S. Loke
<b>Total Number of Pages in This Submission</b>		<b>Attorney Docket Number</b>	
		0756-2062	

<b>ENCLOSURES (check all that apply)</b>		
<input type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input checked="" type="checkbox"/> Amendment / Reply <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement and Notification of Related Application <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/ Incomplete Application <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Assignment Papers <i>(for an Application)</i> <input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert to a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s)	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Other
<b>Remarks</b>		<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 19-2380 for the above identified docket number.

<b>SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT</b>	
Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Nixon Peabody LLP 8180 Greensboro Drive Suite 800 McLean, VA 22012
Signature	
Date	October 15, 2001

<b>CERTIFICATE OF MAILING</b>	
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UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )  
Shunpei YAMAZAKI ) Group Art Unit: 2811  
Serial No. 09/433,705 ) Examiner: S. Loke  
Filed: November 4, 1999 )  
For: METHOD OF FABRICATING )  
A SEMICONDUCTOR DEVICE )

#15/B  
11-13-01  
Payton

**AMENDMENT AND RESPONSE TO NON-COMPLIANT AMENDMENT**

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the *Notice of Non-Compliant Amendment* of September 13, 2001, please amend the subject application as follows:

**IN THE CLAIMS:**

Subt C<sup>2</sup>

Please amend claim 13.

13. (Amended) A semiconductor device comprising:  
a first thin film transistor comprising:  
a semiconductor island on an insulating surface;  
a channel region in the semiconductor island;  
~~at least an LDD region being contact with the channel region and including a first impurity region and a second impurity region, said first impurity region being in contact with the channel region and said second impurity region being in contact with the first impurity region;~~  
~~at least a third impurity region being in contact with the second impurity region; a gate electrode being formed over the semiconductor island with a gate insulating film interposed therebetween and having a first gate electrode and a second electrode being formed on the first gate electrode,~~  
wherein the first gate electrode has at least a taper portion and a flat portion,  
wherein the first impurity region is overlapped with the taper portion of the first gate electrode with the gate insulating film interposed therebetween,